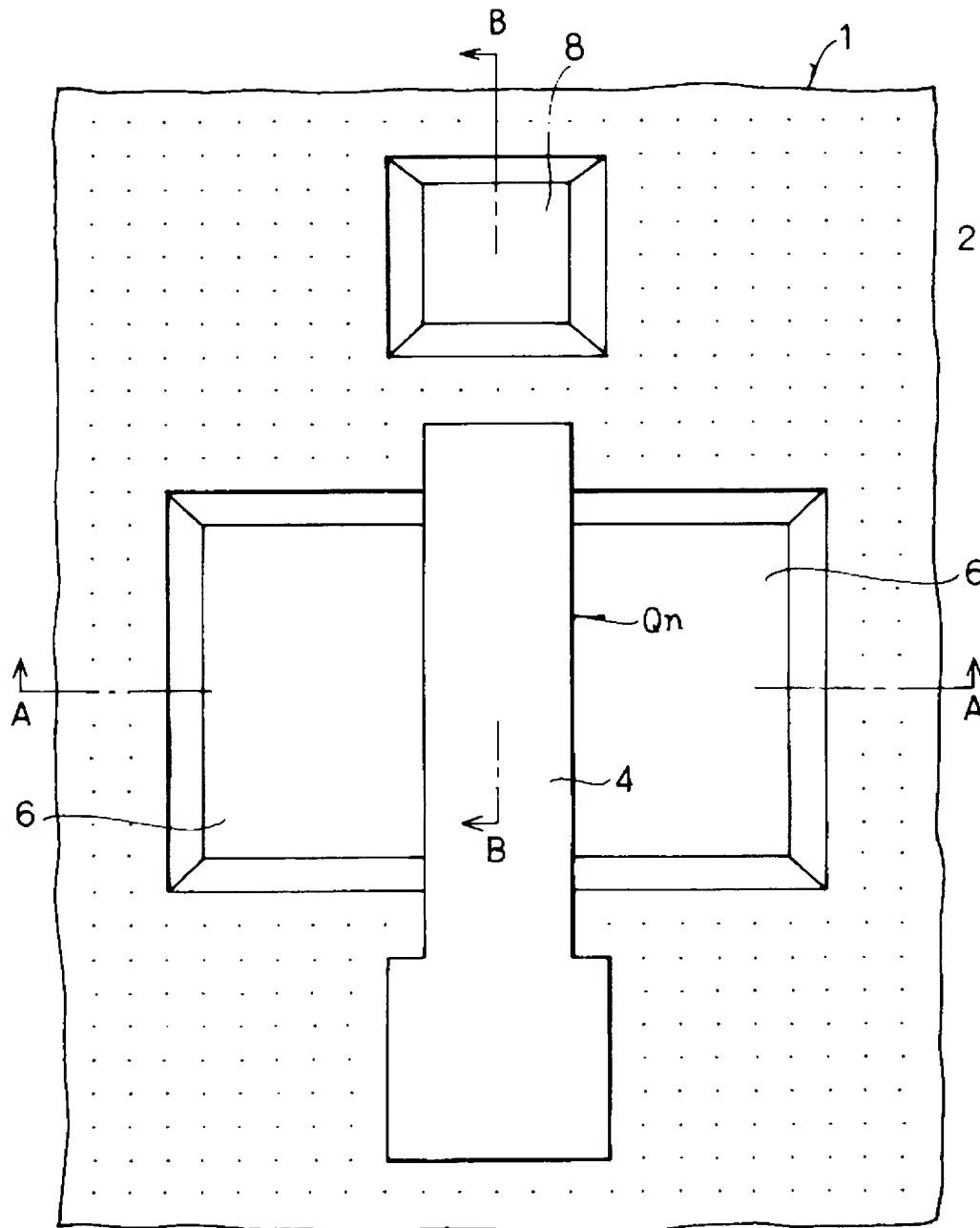


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【図1】

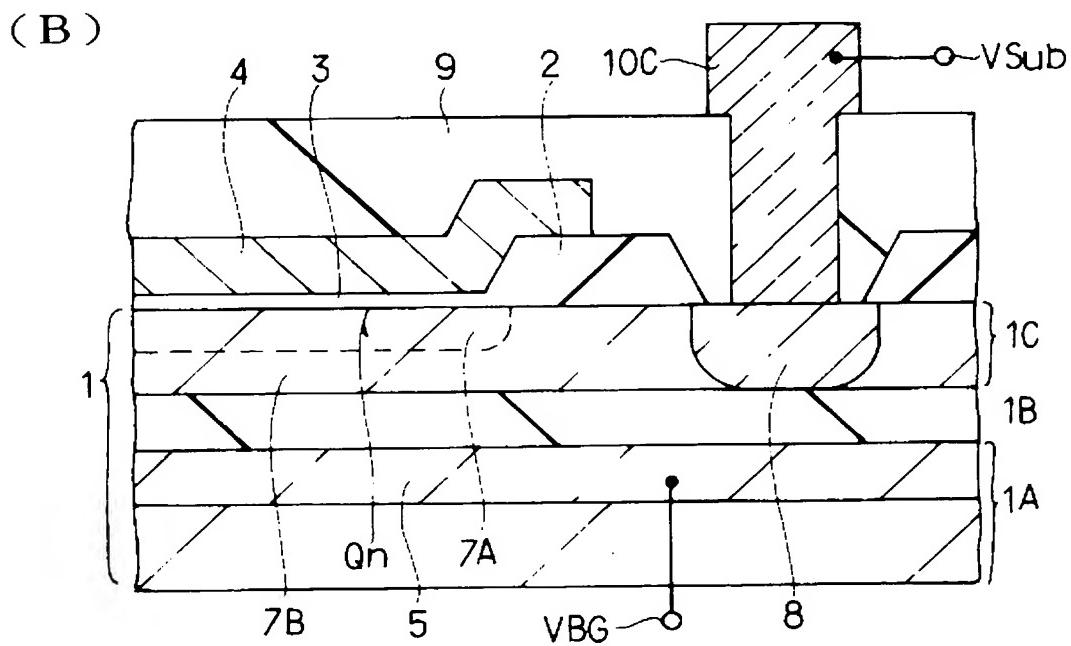
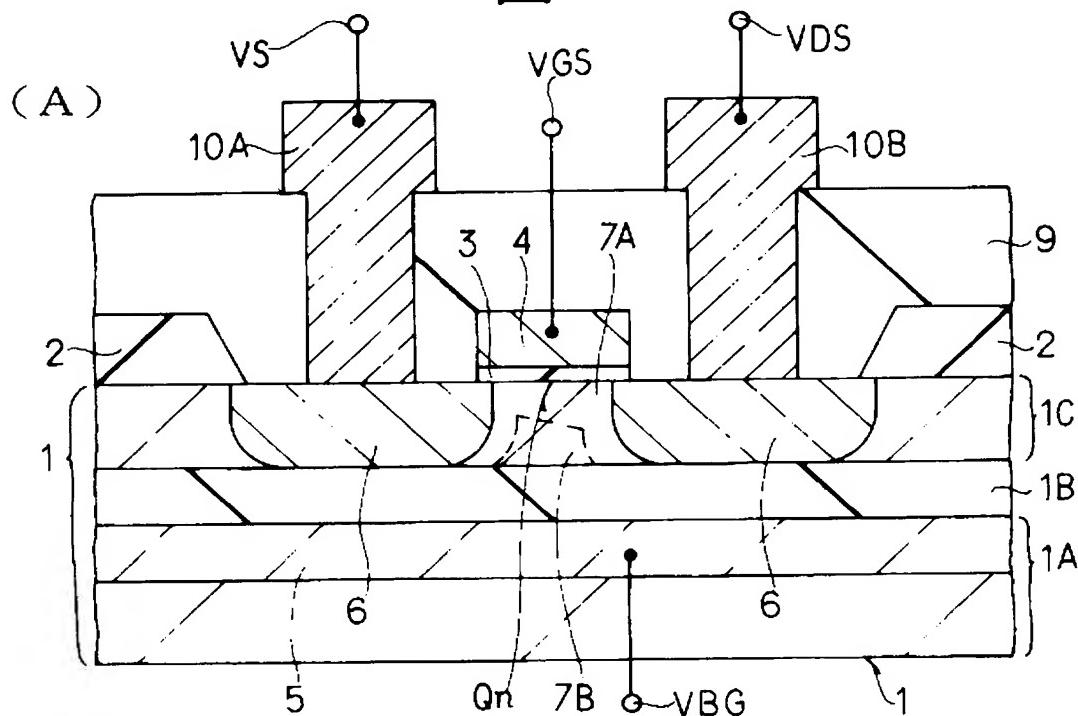
図1



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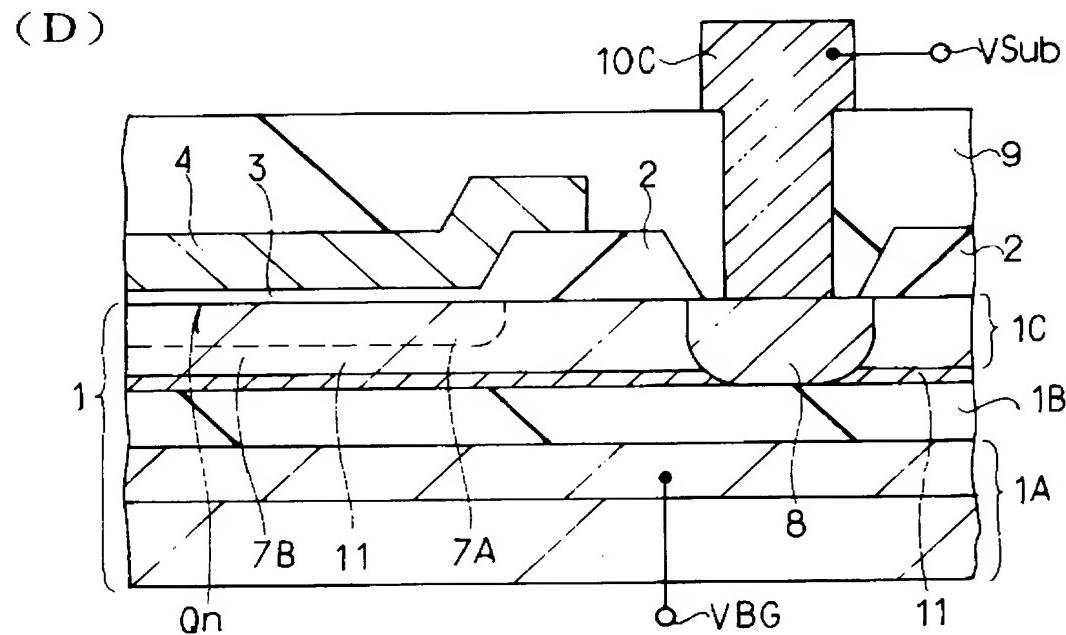
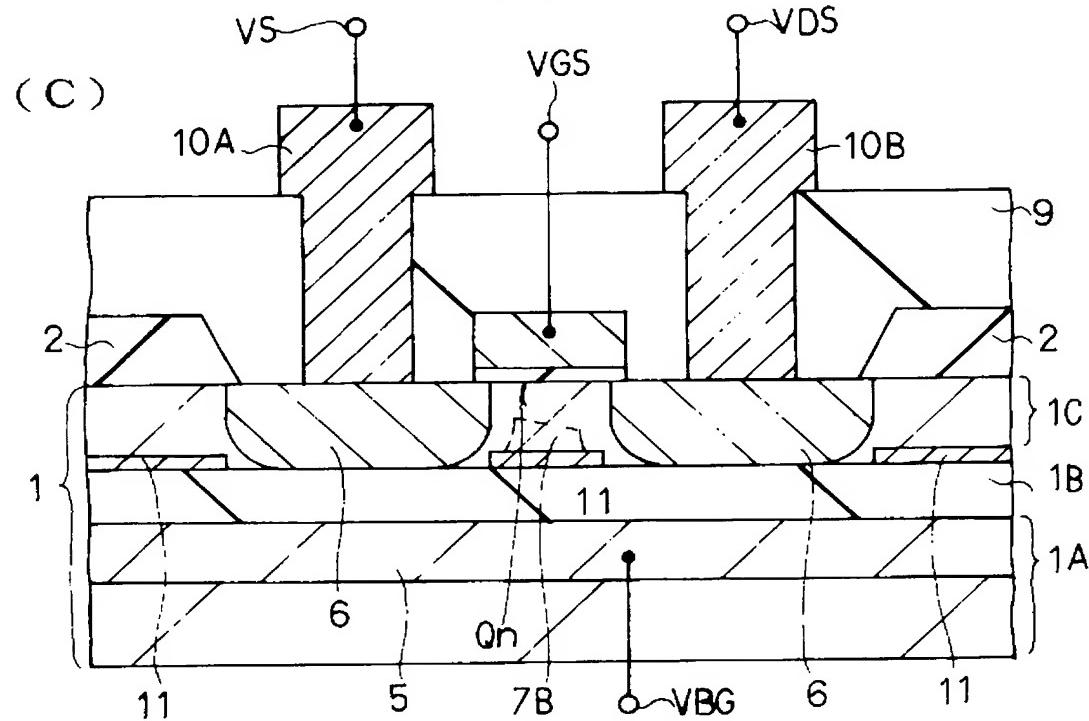
【FIG 2】

FIG 2



【図3】

図3

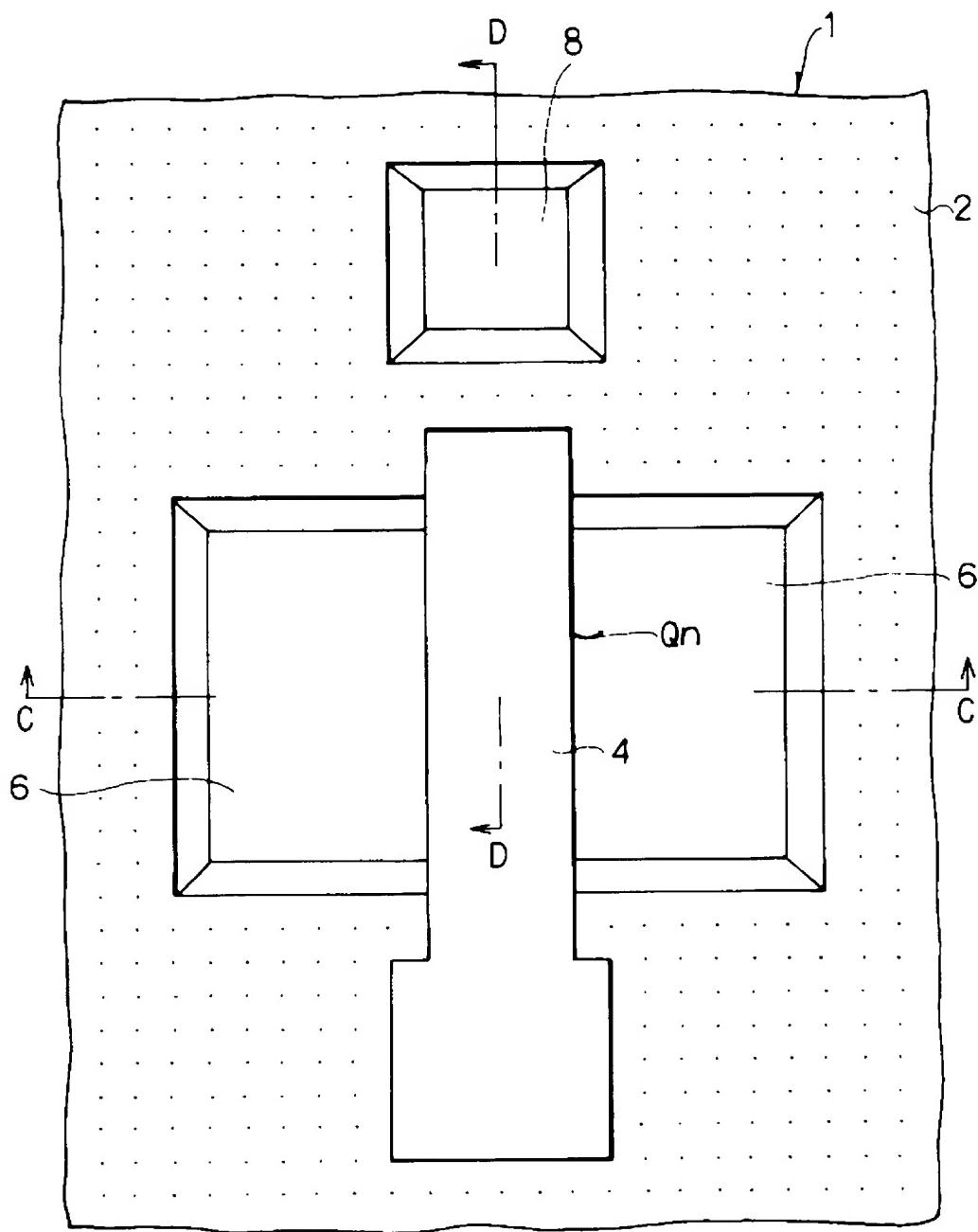


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【図4】

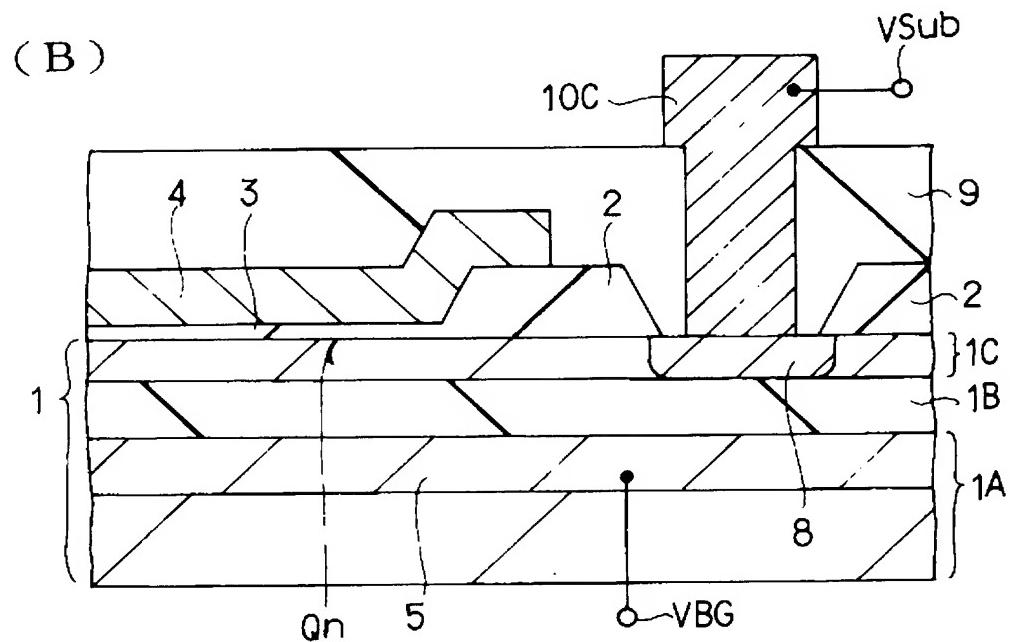
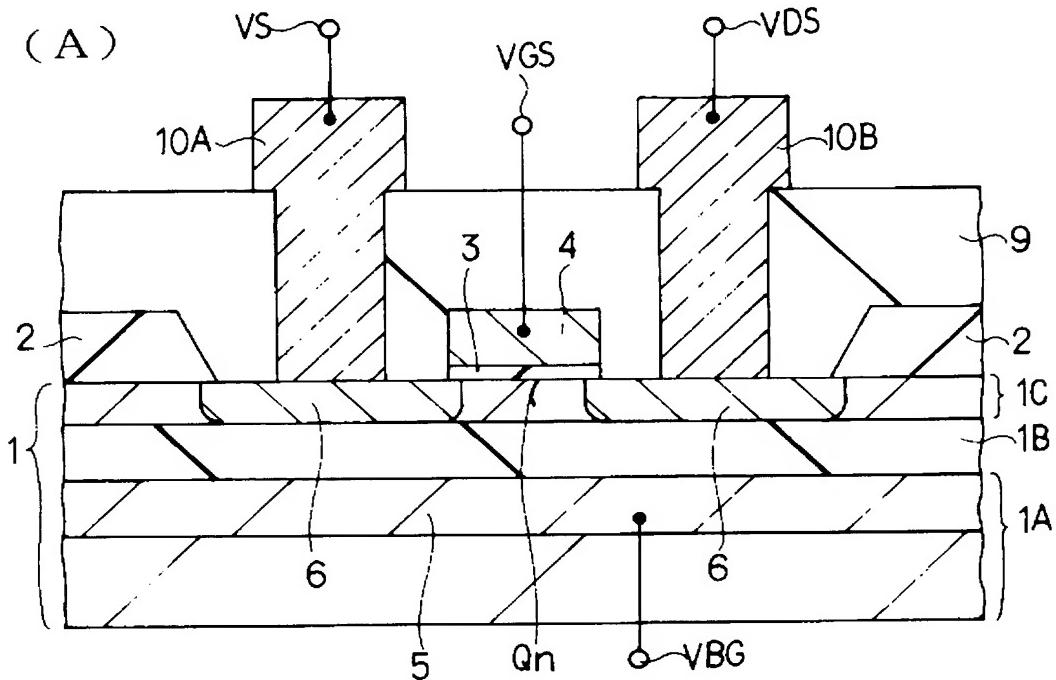
図4



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【図5】

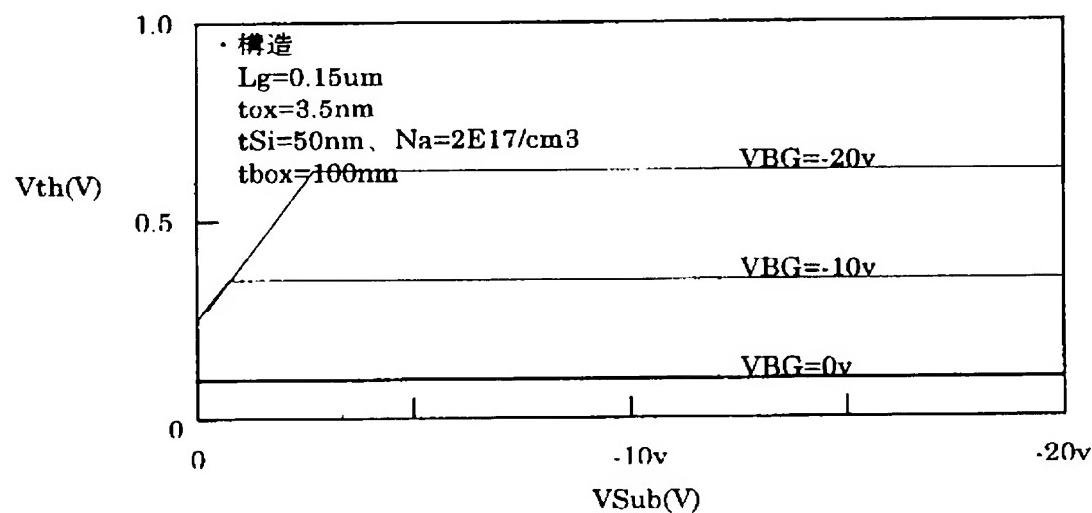
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【図 6】

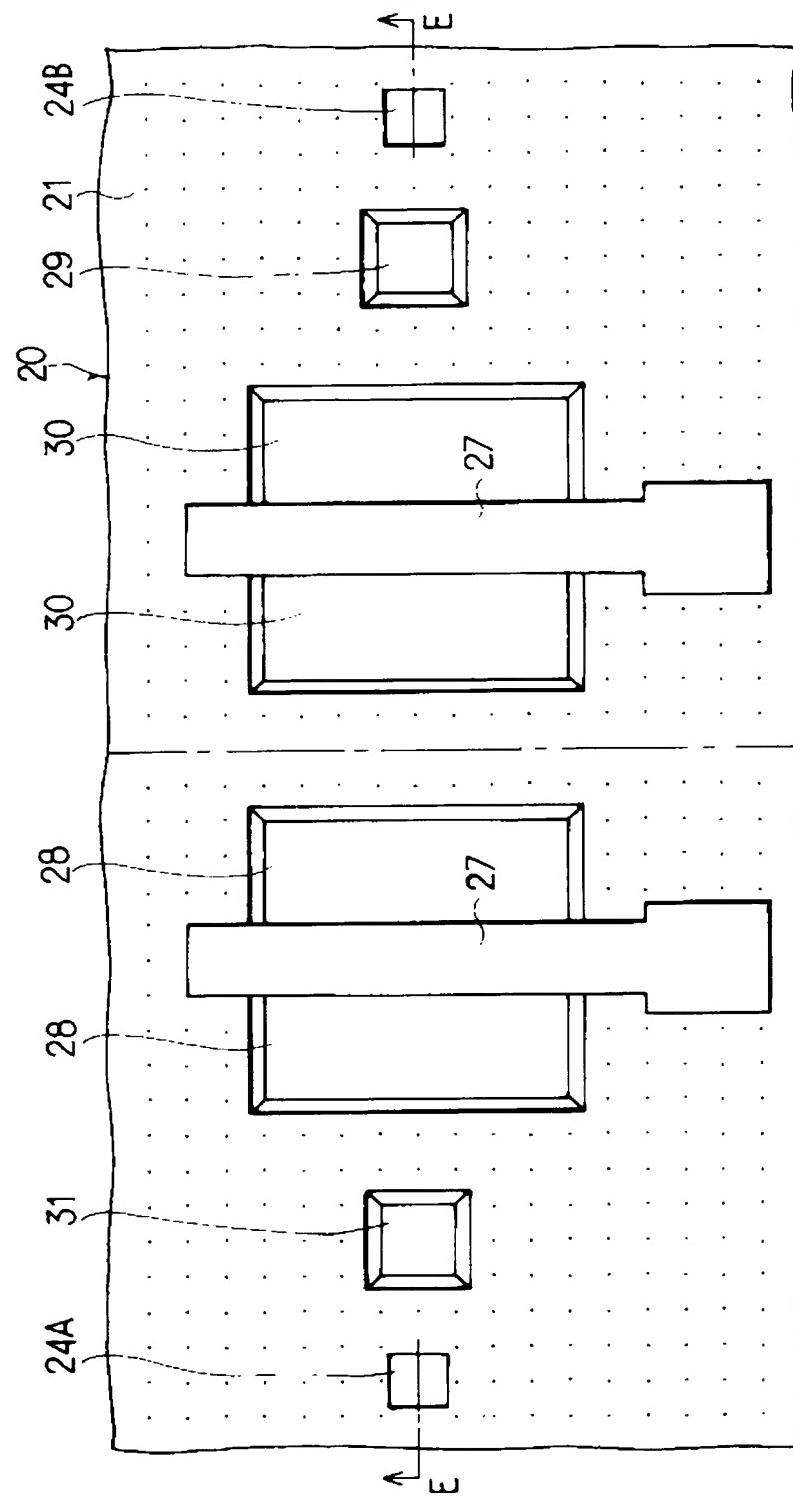
図 6



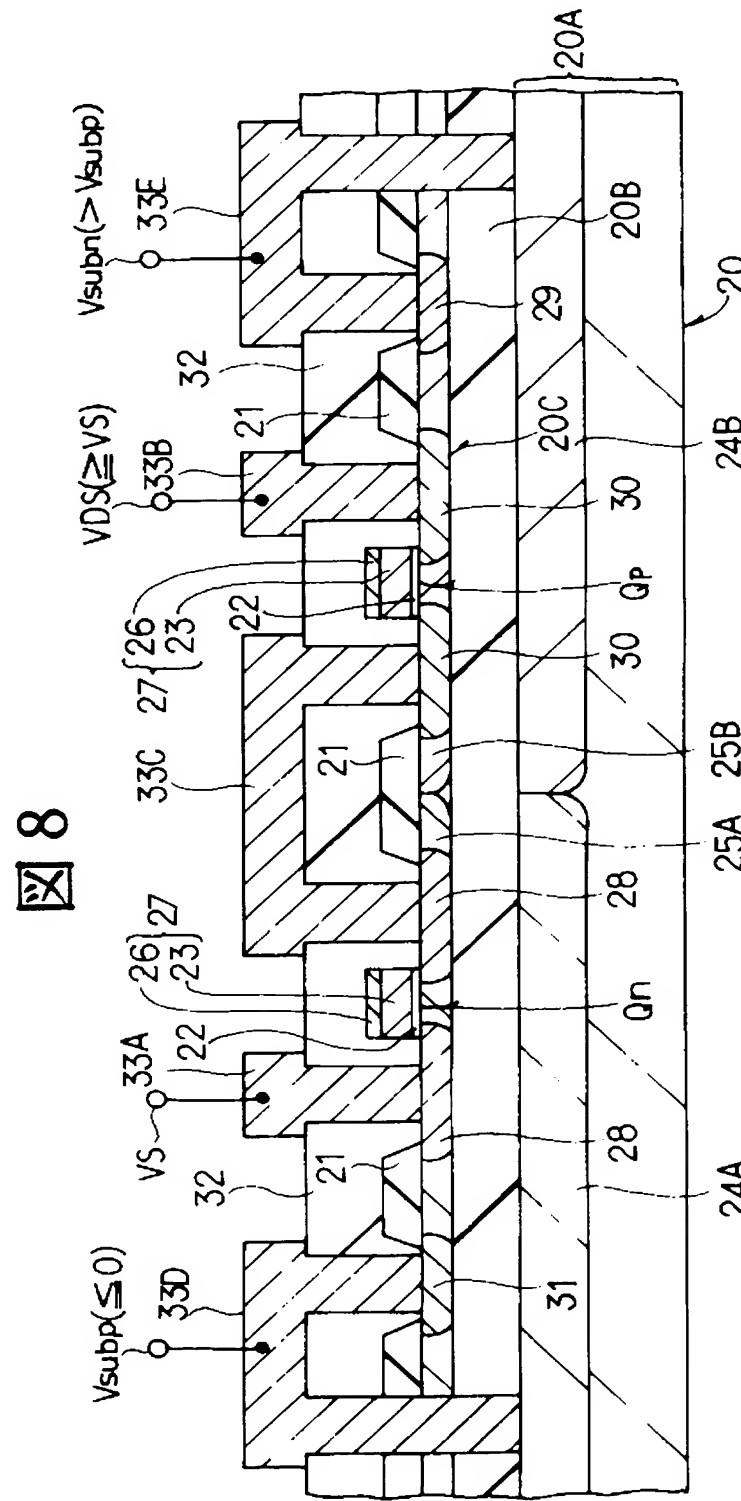
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【FIG 7】

FIG 7

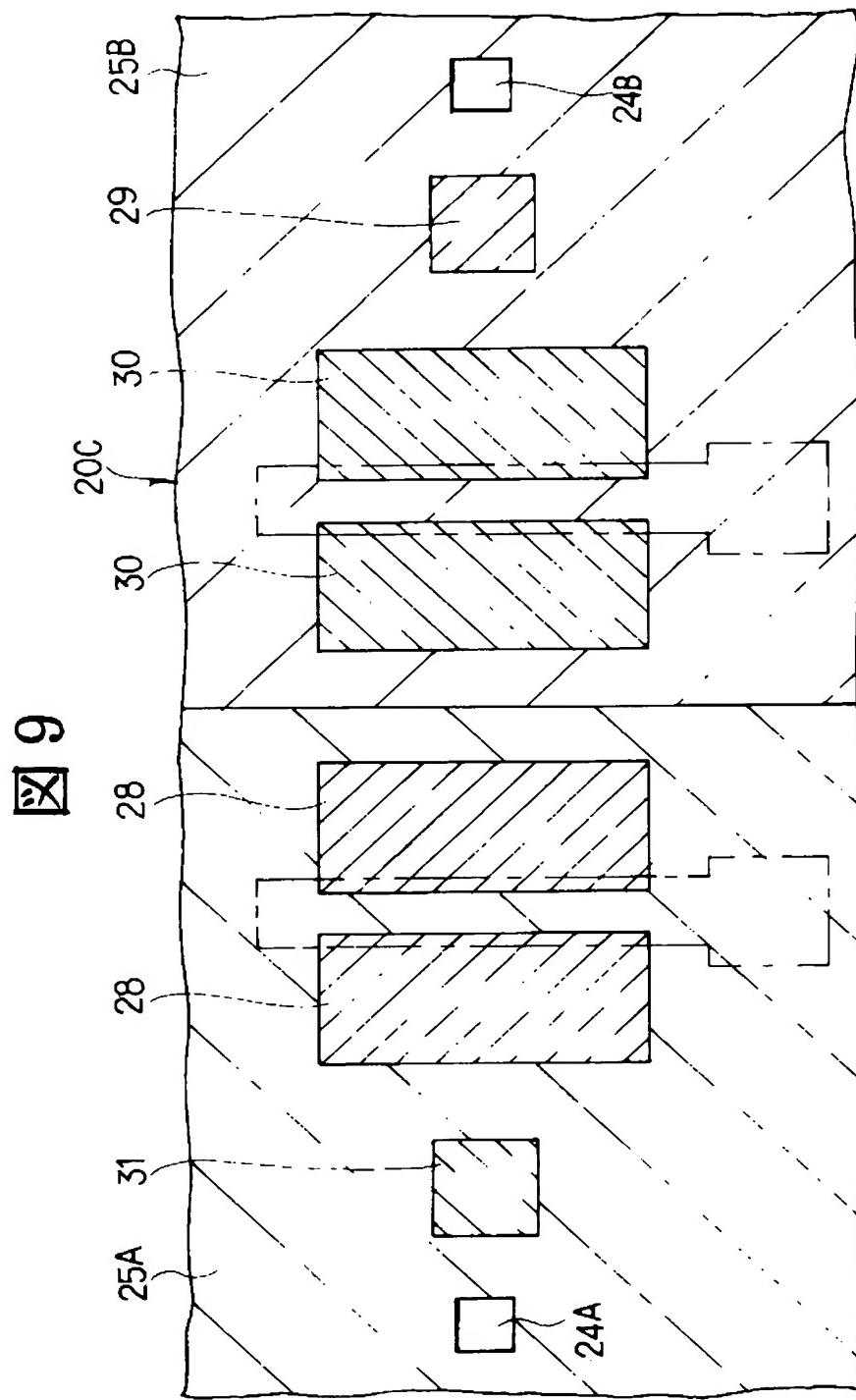


【図 8】





【図9】

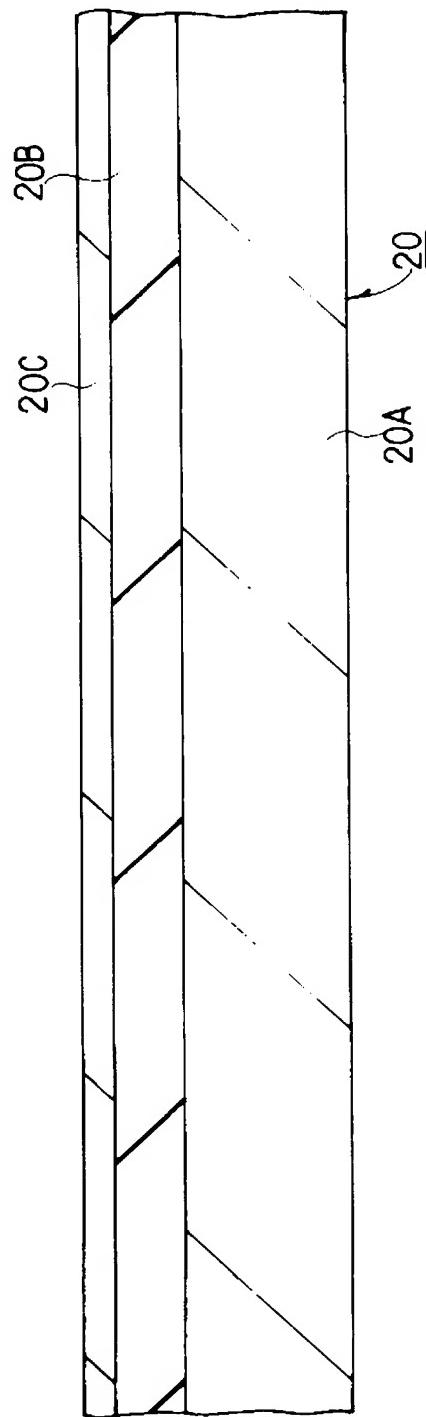




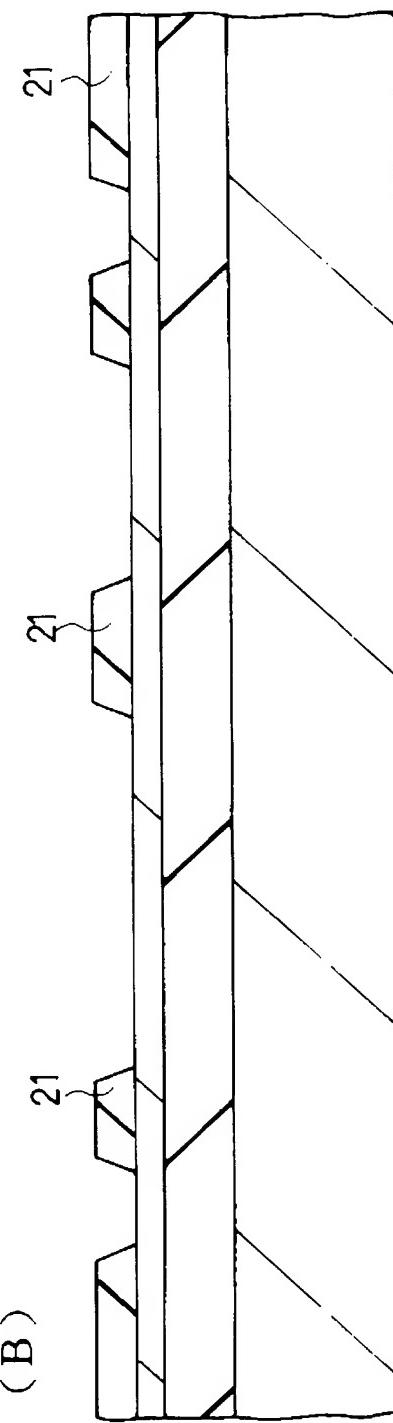
【図10】

図10

(A)



(B)

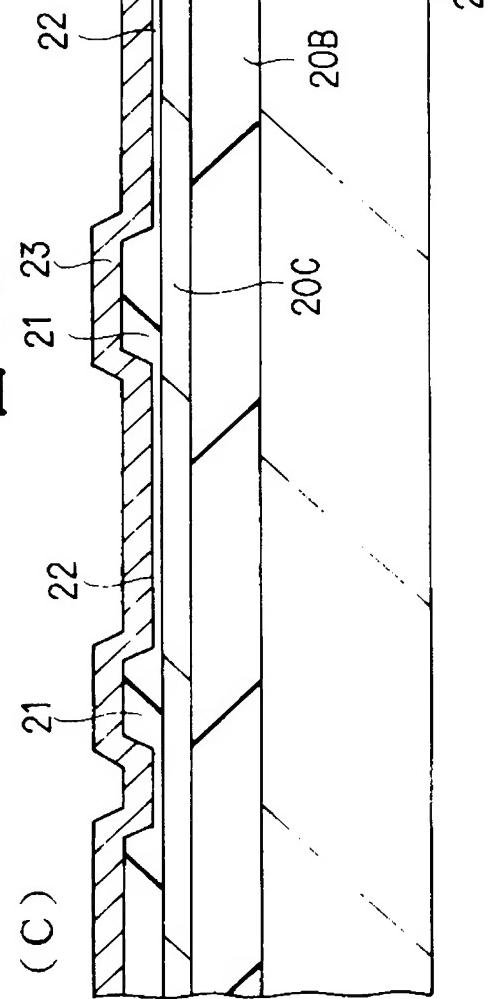




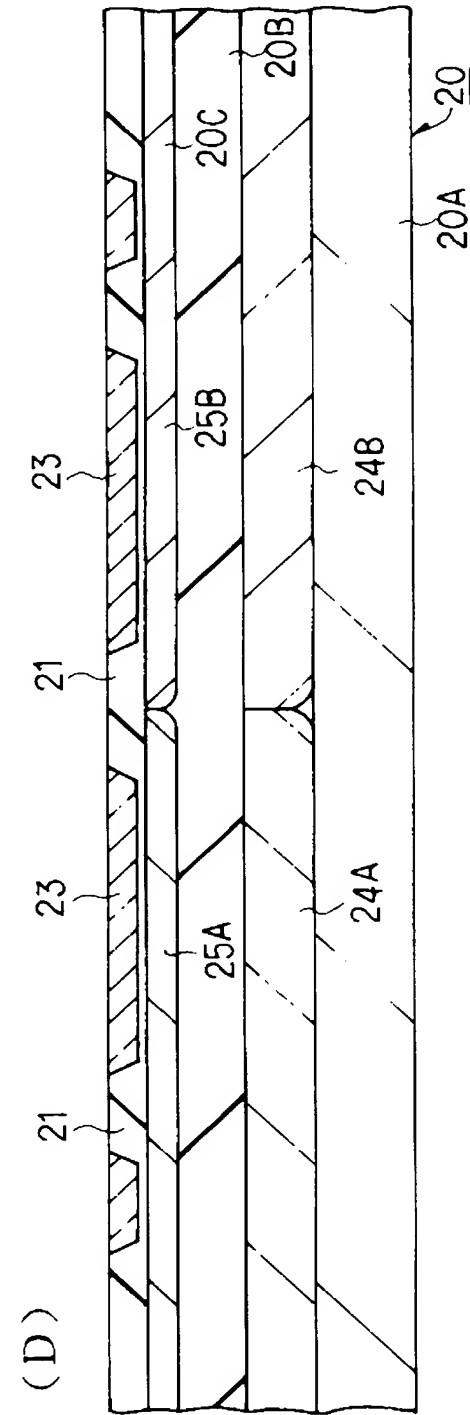
【図11】

図11

(C)



(D)



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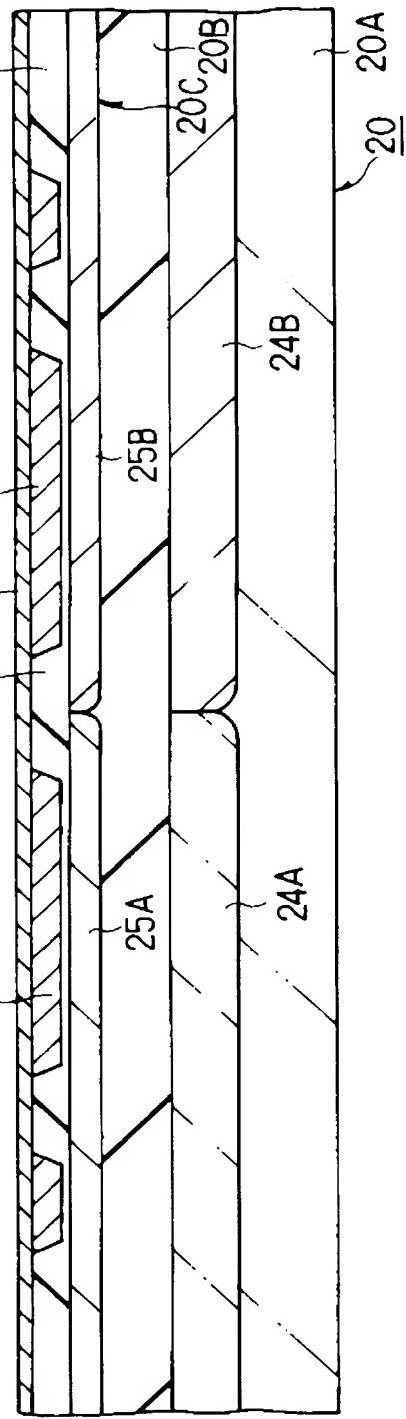
【図 12】

図 12

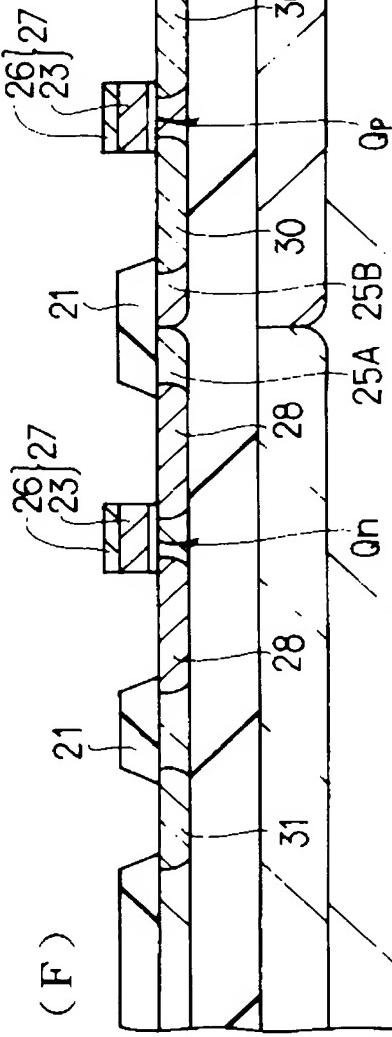
(E)

23
21
26
23

21



(F)

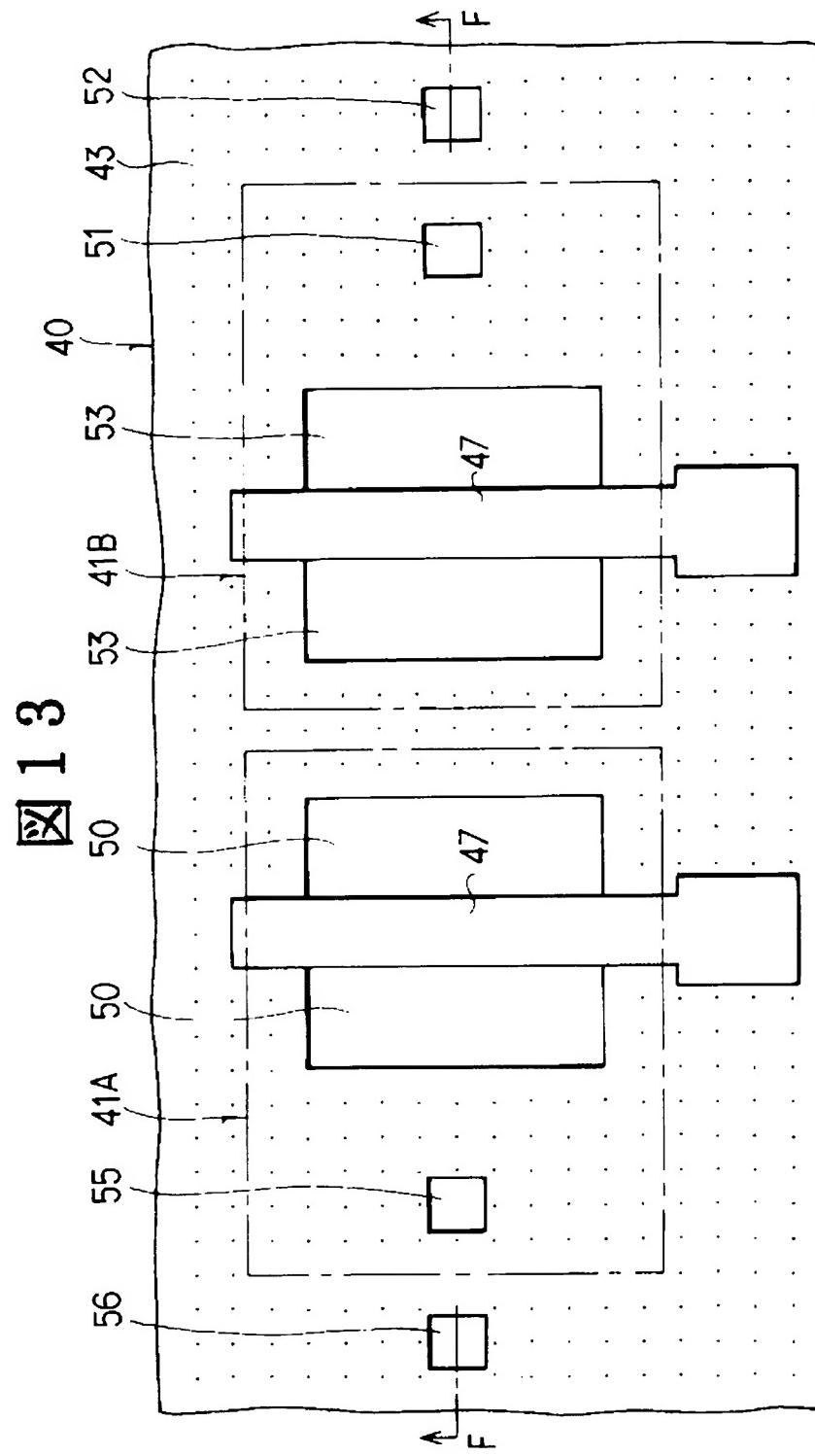


20
20A

20
20A

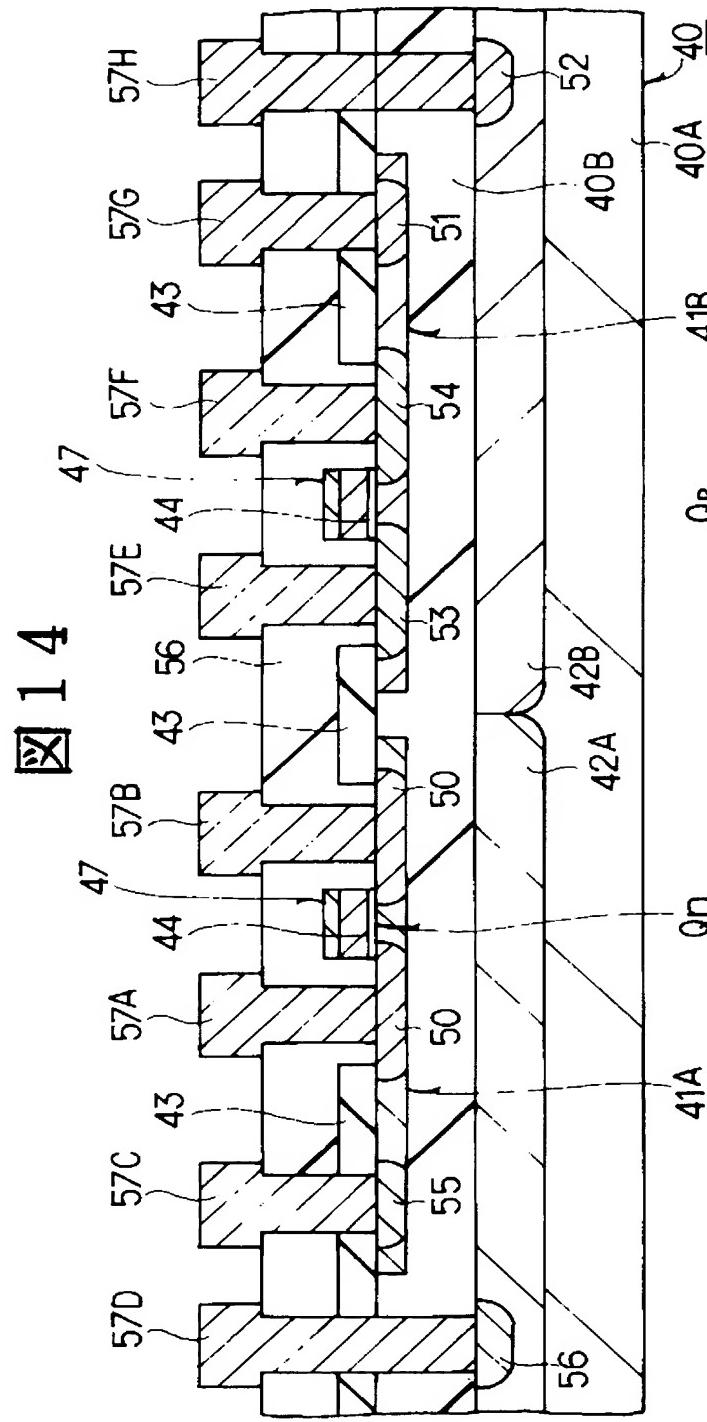
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【図13】



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【図14】

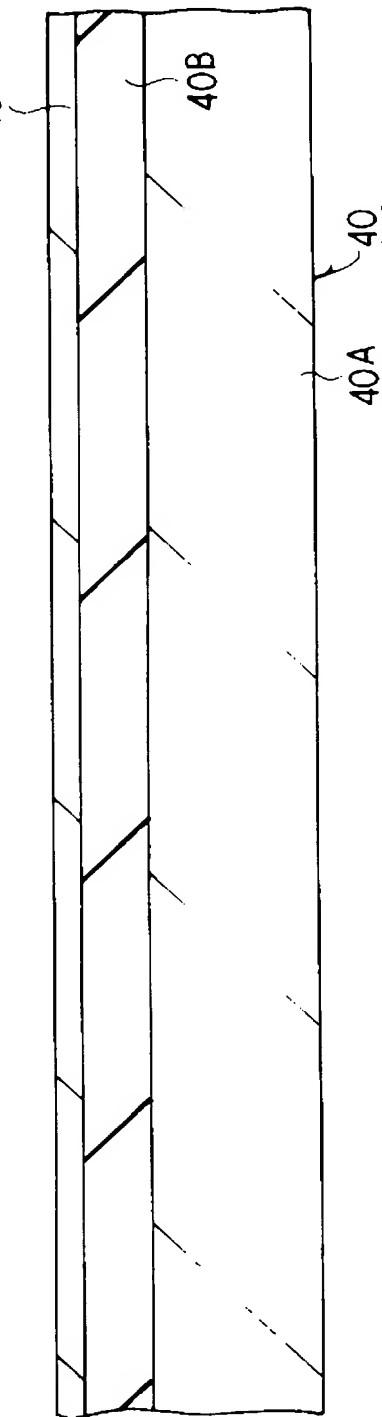


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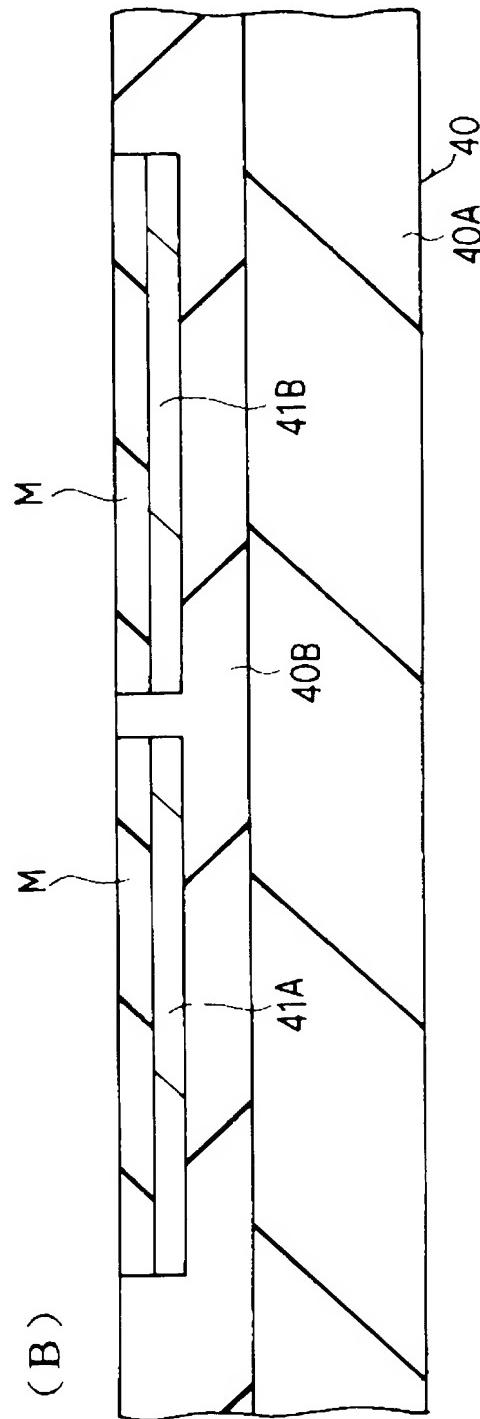
【図15】

図15

(A)



(B)

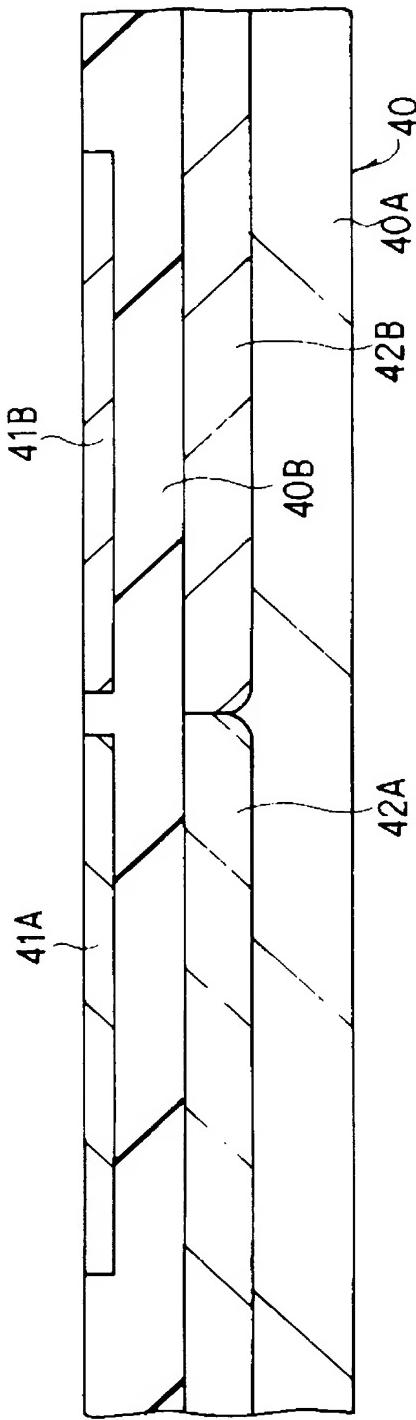




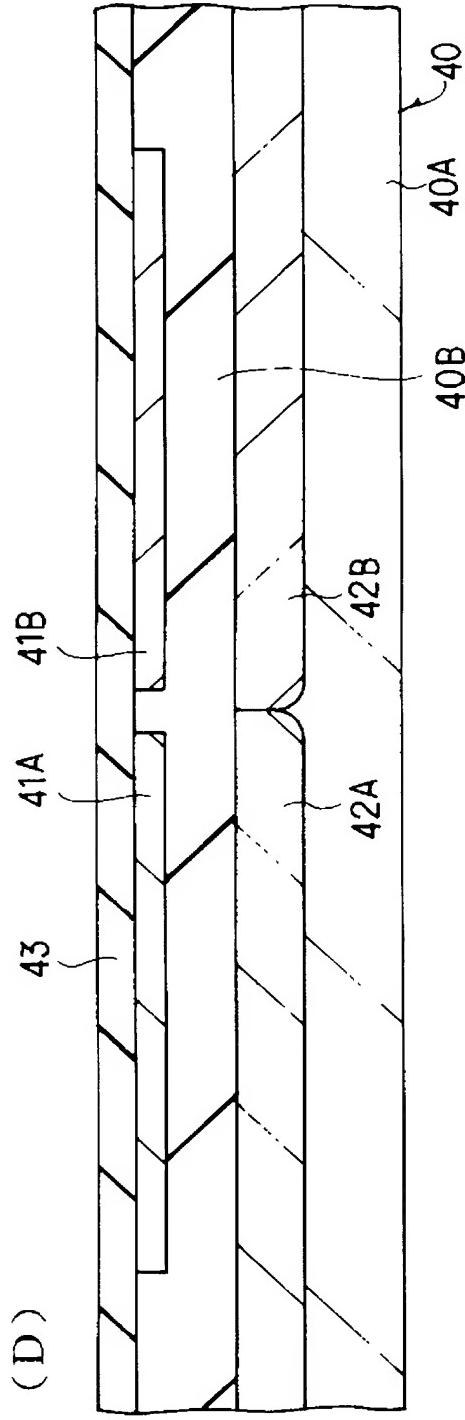
【图 16】

(C)

图 16



(D)

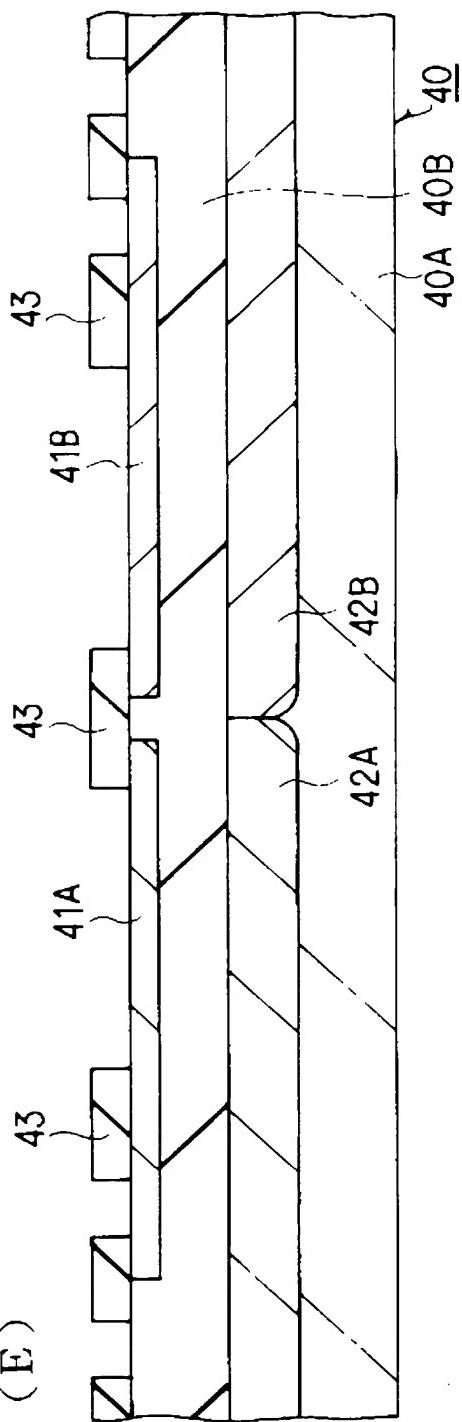


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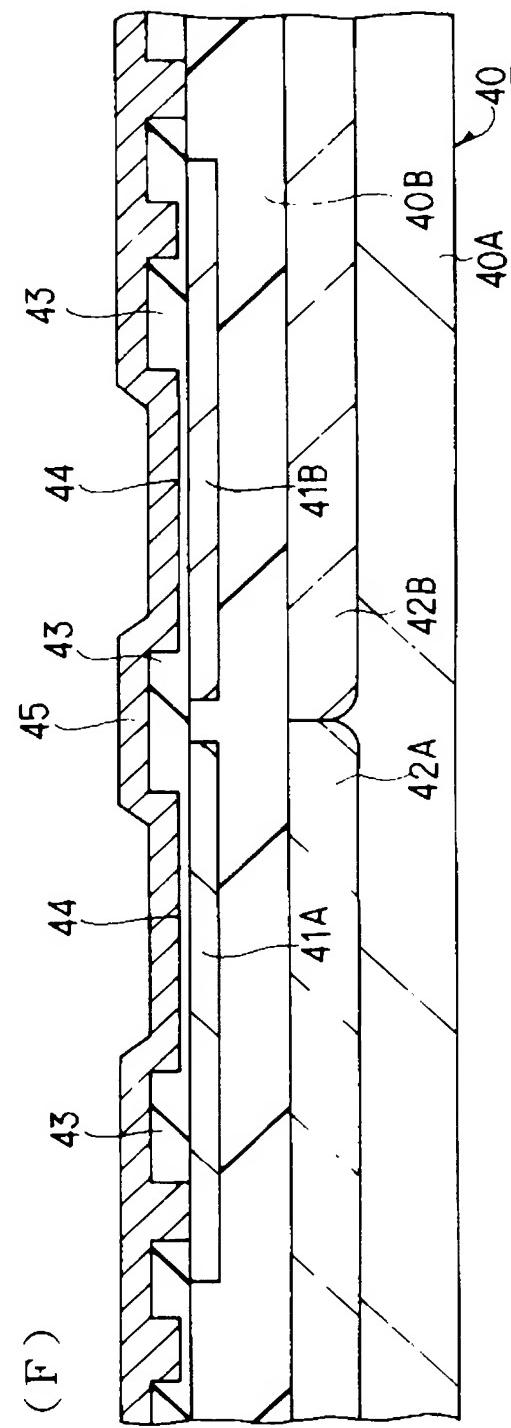
【図 17】

図 17

(E)



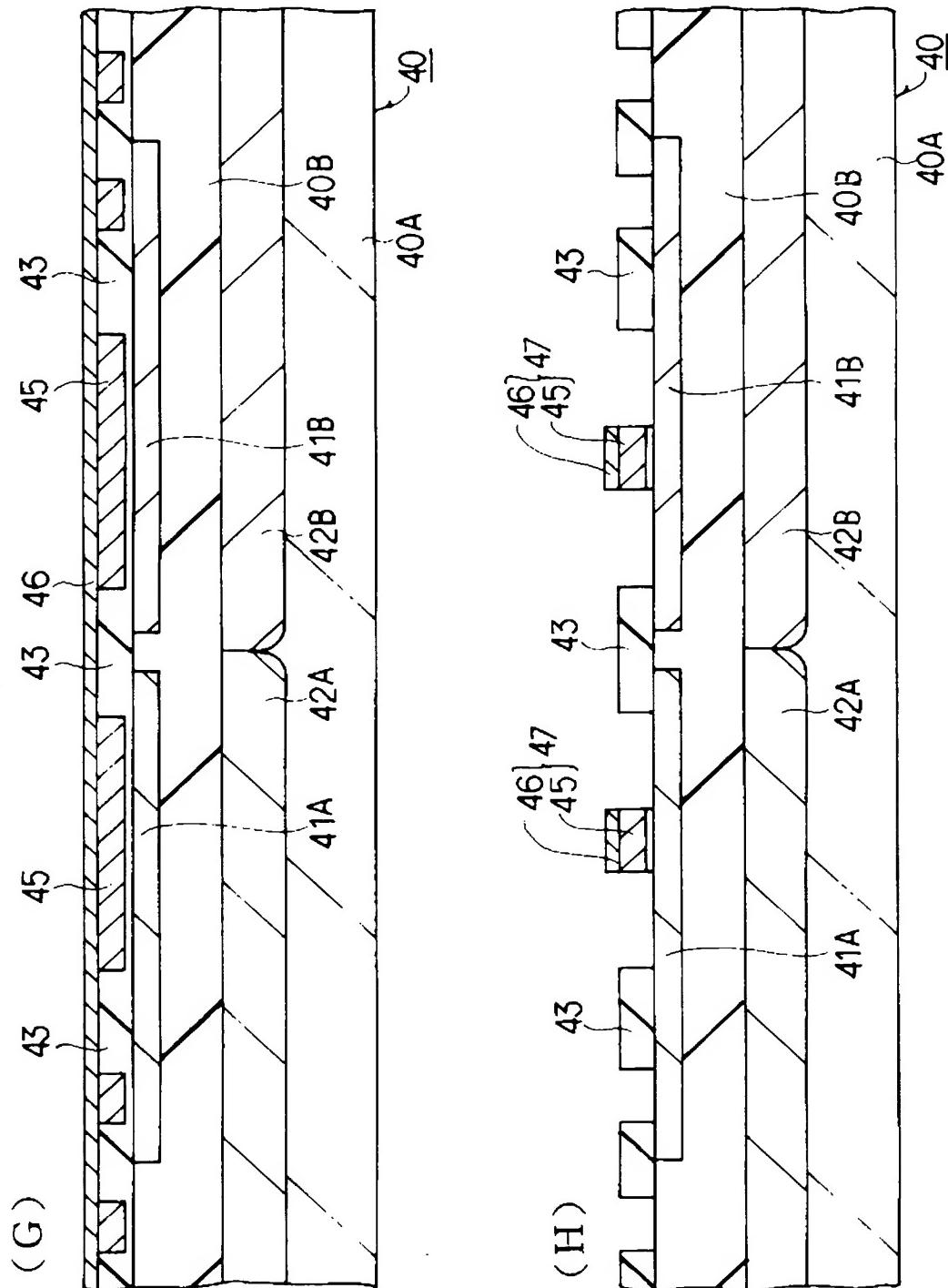
(F)



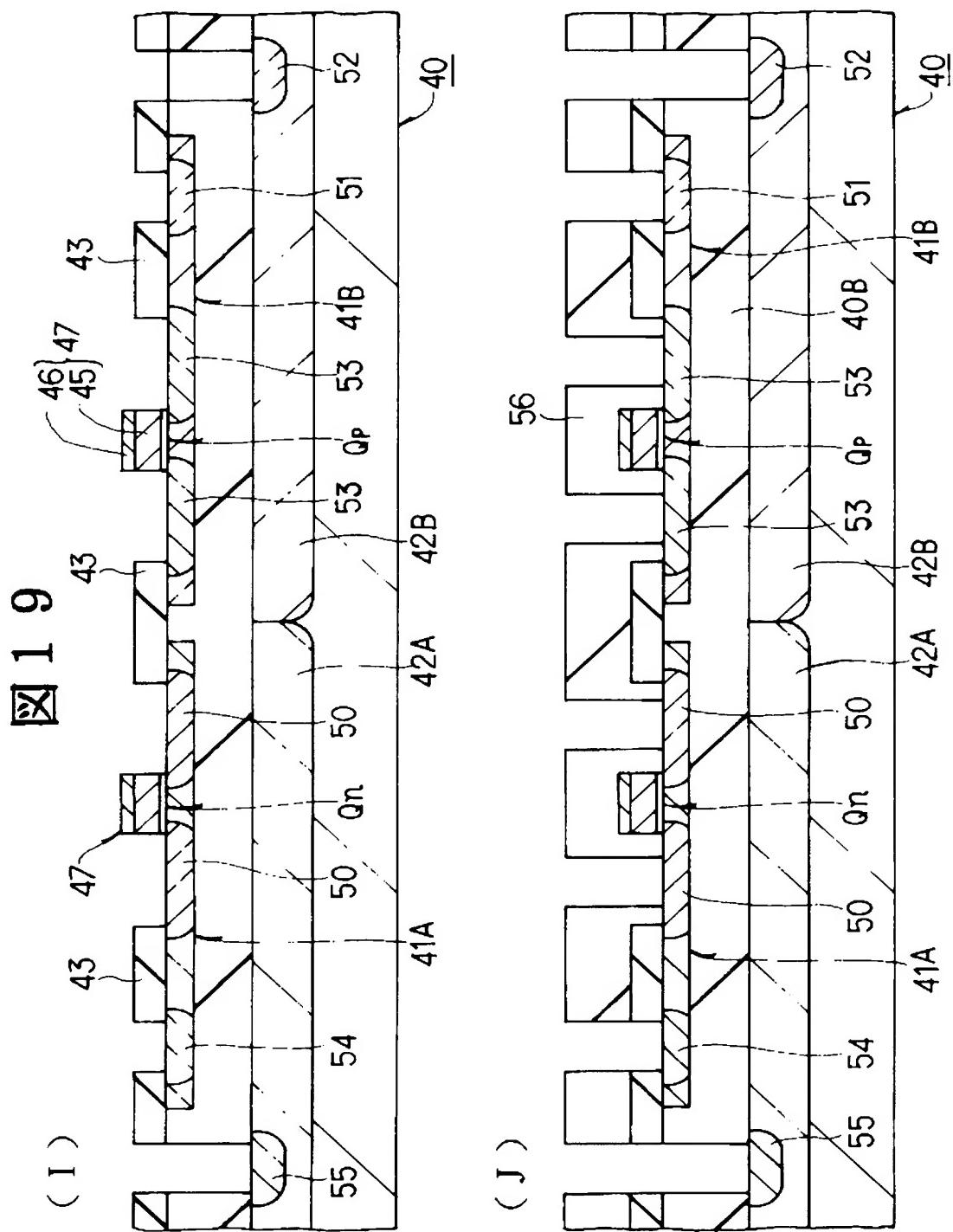
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【图18】

图18

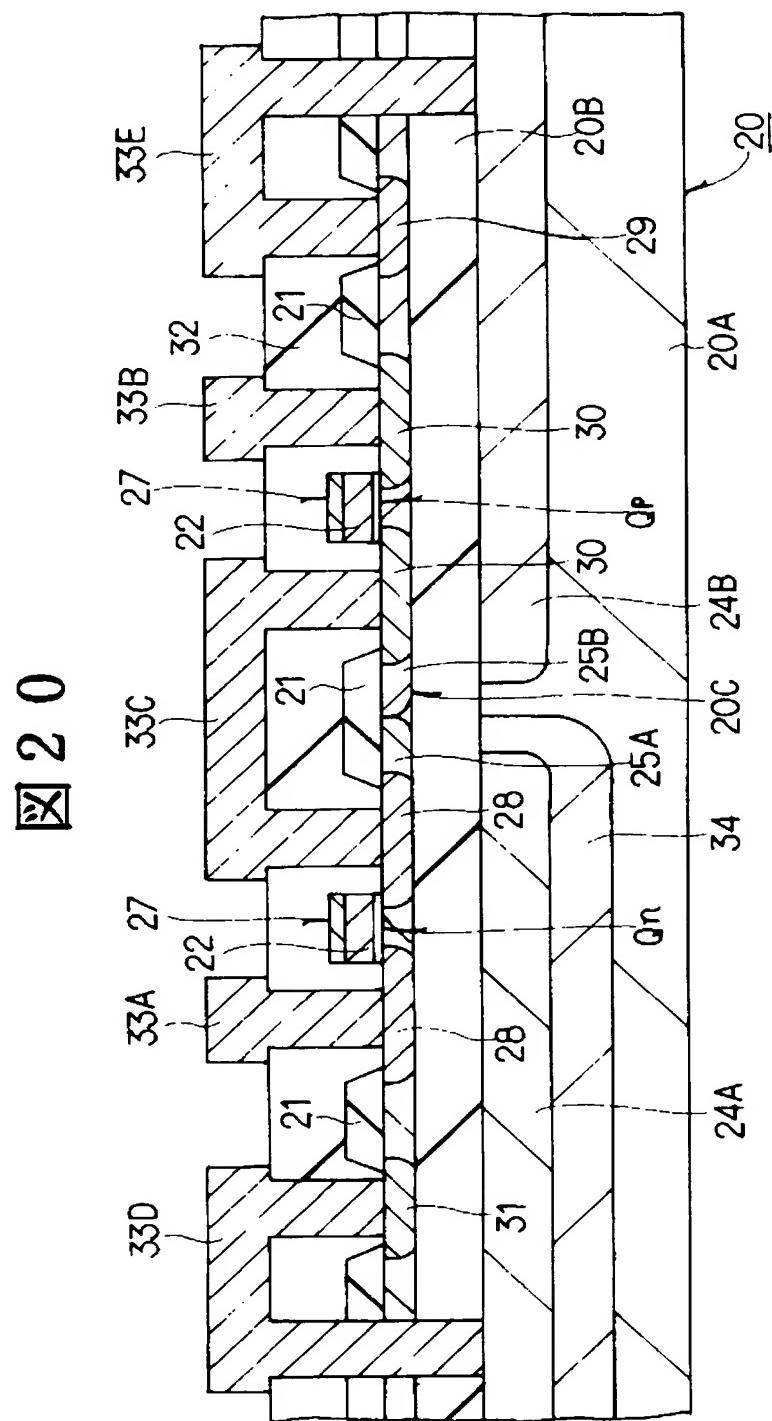


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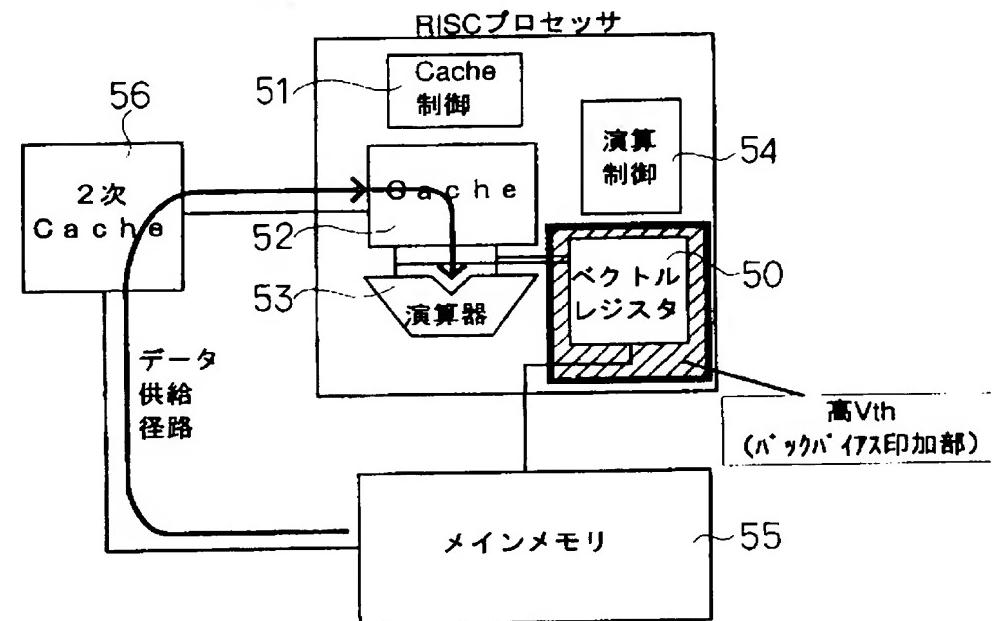
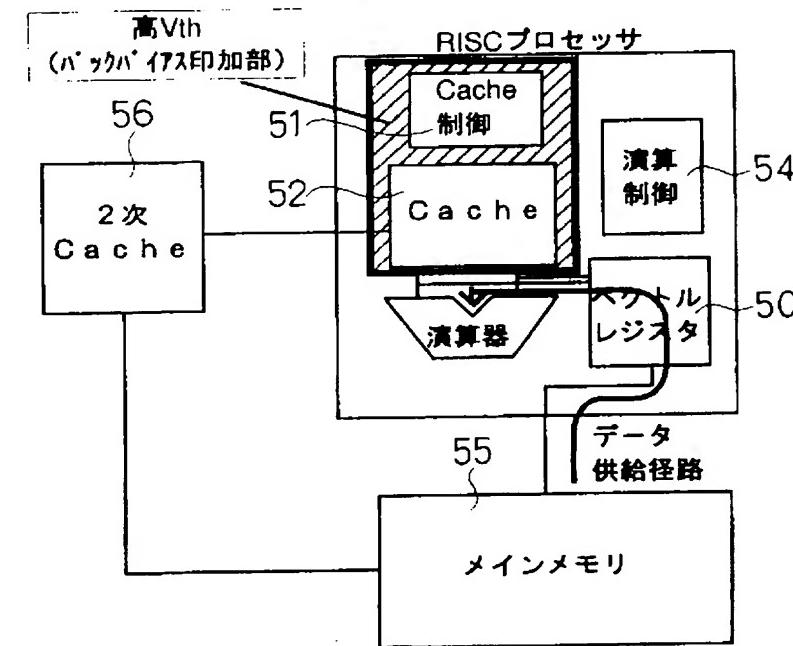
【图20】



【図21】

図21

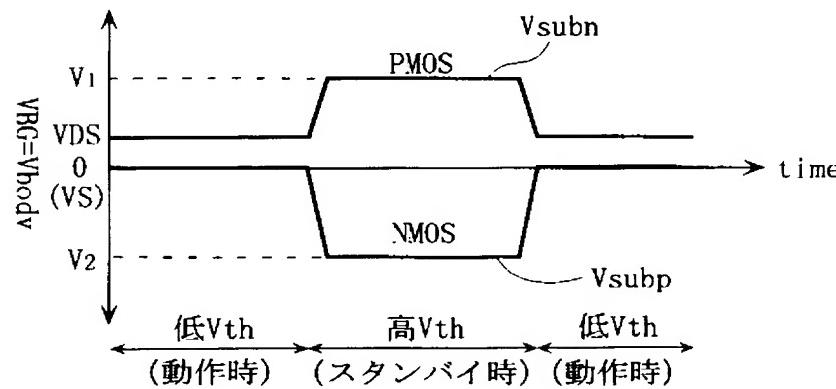
(1) 通常動作モード

(2) 大量データ数値計算モード
(ベクトル演算モード)



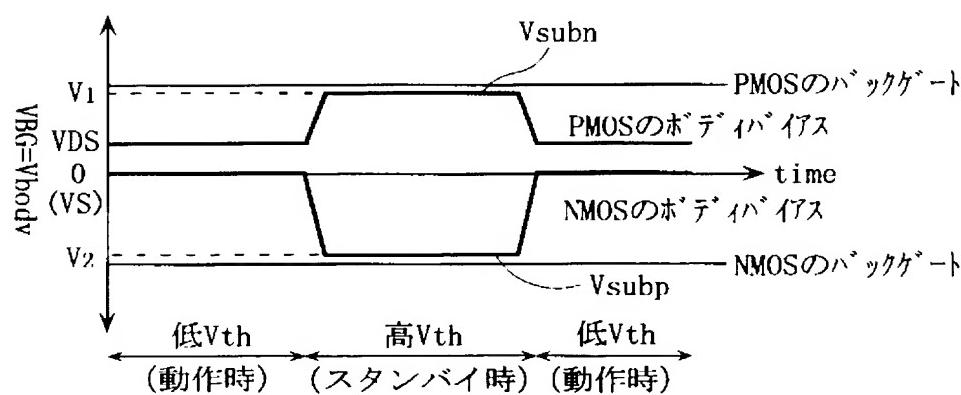
【図22】

図22



【図23】

図23



【書類名】 要約書

【要約】

【課題】 絶縁層上の半導体層に構成された電界効果トランジスタのドレイン耐圧が低くなる。また、閾値電圧が不安定になる。